

Features

- Freq: DC~4GHz
- Insertion Loss: 0.5 dB
- Isolation: 30 dB
- Control Voltage: 0/+5V or 0/-5V
- Chip Size: 0.625mm×0.6mm×0.1mm

General Description

The HG123KB is a reflective GaAs pHEMT SPDT switch chip. Covering DC to 4 GHz, this switch offers isolation of 30 dB and extremely low insertion loss of 0.5 dB. This switch operates using a positive control voltage of 0/+5V or negative control voltage of 0/-5V ,and requires no bias supply.

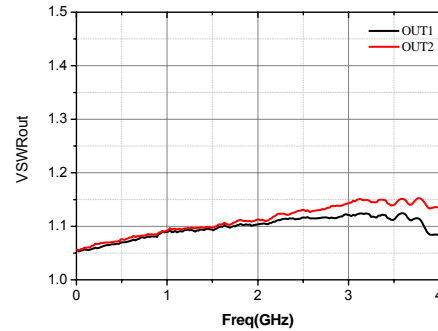
Electrical Specifications($T_A=25^\circ\text{C}$)

Parameter	Min.	Typ.	Max.
Frequency Range(GHz)	DC~4		
Input VSWR	-	1.1	-
Output VSWR	-	1.1	-
Insertion Loss(dB)	-	0.5	-
Isolation(dB)	-	30	-

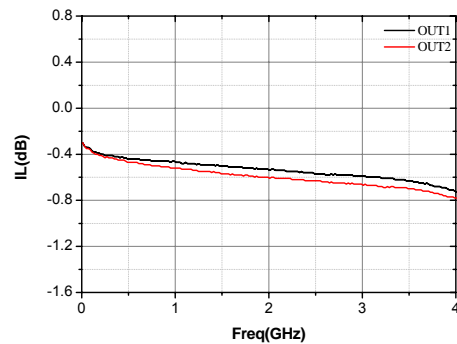
Truth Table(0: 0V or -5V, 1: +5V or 0V)

SW1	SW2	RFC to RF1	RFC to RF2
1	0	ON	OFF
0	1	OFF	ON

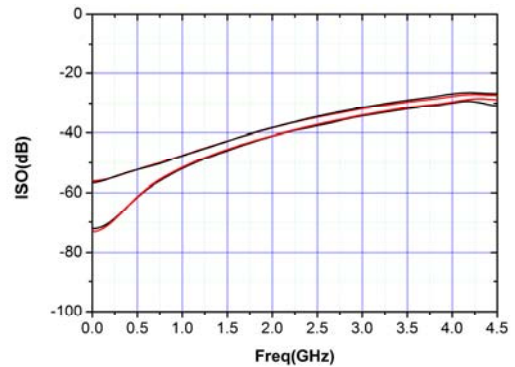
Output VSWR



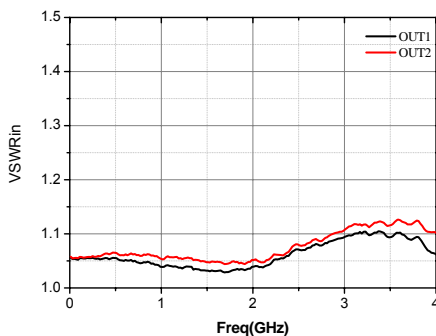
Insertion Loss



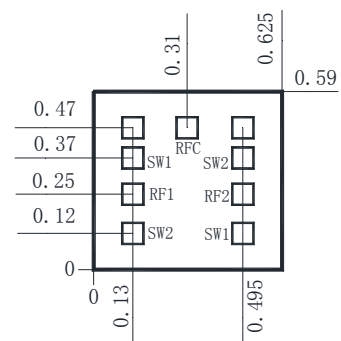
Isolation



Input VSWR



Outline Drawing (mm)



Absolute Maximum Ratings

Control Voltage	±5.5V
RF Input Power	+27dBm
Operating Temperature	-55℃~125℃
Storage Temperature	-65℃~150℃

Notes:

1. The chip should be stored in a dry and nitrogen environment, and used in a clean environment.
2. GaAs material is brittle, can not touch the surface of the chip, must be careful when using.
3. The chip is welding with conductive adhesive or alloy (alloy temperature should not exceed 300℃, and no more than 30 sec.), and should make it fully grounded.
4. The chip microwave port and substrate gap is not exceeding 0.05mm, with $\Phi 25\mu\text{m}$ double gold wire bonding, suggested length of gold wire 250~400 μm .
5. Chip microwave port without DC blocking capacitor.
6. The chip is sensitive to static electricity, and should be protected against static electricity during storage and use.